



# BRT40N210P2

## N-channel Enhancement Mode Power MOSFET

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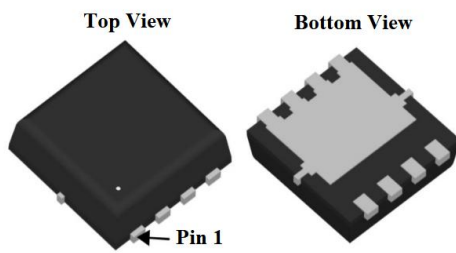
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## FEATURES

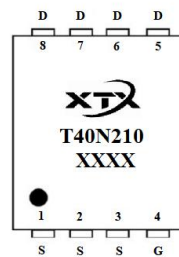
- ◆ 40V, 210A
- ◆  $R_{DS(ON)} < 1.6m\Omega @ V_{GS} = 10V$
- ◆  $R_{DS(ON)} < 3.0m\Omega @ V_{GS} = 4.5V$
- ◆ Advanced Trench Technology
- ◆ Excellent  $R_{DS(ON)}$  and Low Gate Charge
- ◆ Lead Free

## APPLICATIONS

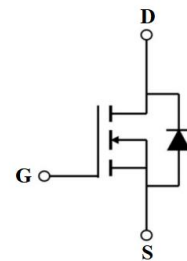
- ◆ Load Switch
- ◆ PWM Application
- ◆ Power Management



PDFN5\*6-8L



Marking and Pin Assignment



Schematic Diagram

## PACKAGE MARKING AND ORDERING INFORMATION

OPN	Marking	Package	Quantity
BRT40N210P2	T40N210	PDFN5*6-8L	5000pcs/Reel

## ABSOLUTE MAXIMUM RATINGS

Symbol	Definition		Ratings	Unit
$V_{DS}$	Drain-to-Source Voltage		40	V
$V_{GS}$	Gate-to-Source Voltage		$\pm 20$	V
$I_D$	Continuous Drain Current	$T_C = 25^\circ C$	210	A
		$T_C = 100^\circ C$	137	A
$I_{DM}$	Pulsed Drain Current <sup>(1)</sup>		840	A
$E_{AS}$	Single Pulsed Avalanche Energy <sup>(2)</sup>		420	mJ
$P_D$	Power Dissipation, $T_C = 25^\circ C$		120	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		1.0	$^\circ C/W$
$T_J, T_{STG}$	Junction & Storage Temperature Range		-55 ~ +150	$^\circ C$

**ELECTRICAL CHARACTERISTICS** (All test condition is  $T_J=25^{\circ}\text{C}$ , unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Off Characteristics						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V	40	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V	-	-	1	uA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V	-	-	±100	nA
On Characteristics						
V <sub>GS(TH)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250uA	1.0	1.7	2.5	V
R <sub>DS(ON)</sub>	Static Drain-Source ON-Resistance <sup>(3)</sup>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 30A		1.35	1.6	mΩ
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 20A		1.7	3.0	mΩ
Dynamic Characteristics						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 20V, f = 1MHz	-	11.39	-	nF
C <sub>oss</sub>	Output Capacitance		-	770	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-	621	-	pF
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> = 0 to 10V V <sub>DS</sub> = 20V, I <sub>D</sub> = 30A	-	95	-	nC
Q <sub>gs</sub>	Gate Source Charge		-	15	-	nC
Q <sub>gd</sub>	Gate Drain("Miller") Charge		-	19	-	nC
Switching Characteristics						
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>GS</sub> = 10V, V <sub>DD</sub> = 20V I <sub>D</sub> = 30A, R <sub>G</sub> = 3Ω	-	10	-	ns
t <sub>r</sub>	Turn-On Rise Time		-	28	-	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		-	38	-	ns
t <sub>f</sub>	Turn-Off Fall Time		-	9	-	ns
Drain-Source Diode Characteristics						
I <sub>S</sub>	Continuous Source Current		-	-	210	A
V <sub>SD</sub>	Forward on voltage	V <sub>GS</sub> = 0V, I <sub>S</sub> = 30A	-	-	1.2	V
T <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 30A, di/dt = 100A/us	-	-	35	ns
Q <sub>rr</sub>	Reverse Recovery Charge		-	-	24.2	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2.  $E_{AS}$  condition: Starting  $T_J=25^{\circ}\text{C}$ ,  $V_{GS}=35\text{V}$ ,  $R_G=25\Omega$ ,  $L=0.5\text{mH}$ ,  $I_{AS}=41\text{A}$
3. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 0.5\%$ .

## TYPICAL PERFORMANCE CHARACTERISTICS

Figure 1: Output Characteristics

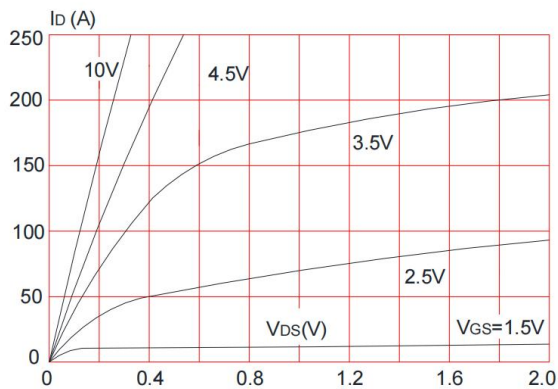


Figure 2: Typical Transfer Characteristics

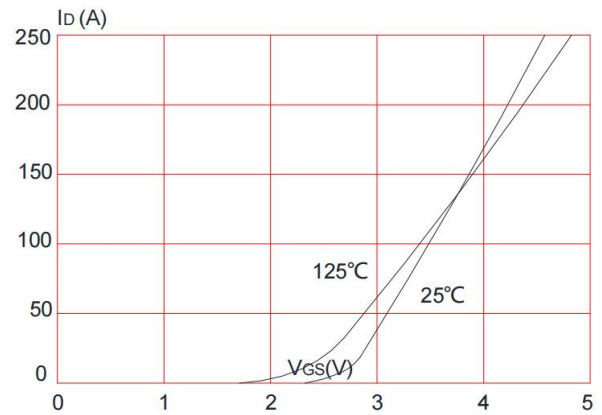


Figure 3: On-resistance vs. Drain Current

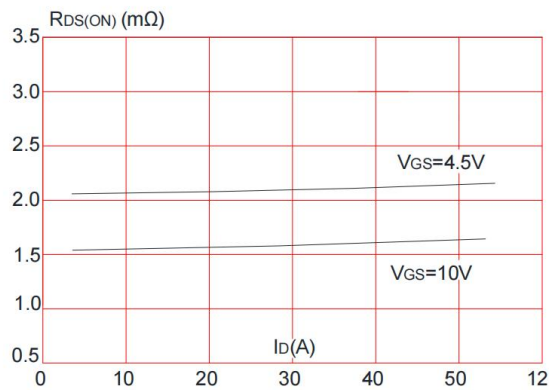


Figure 4: Body Diode Characteristics

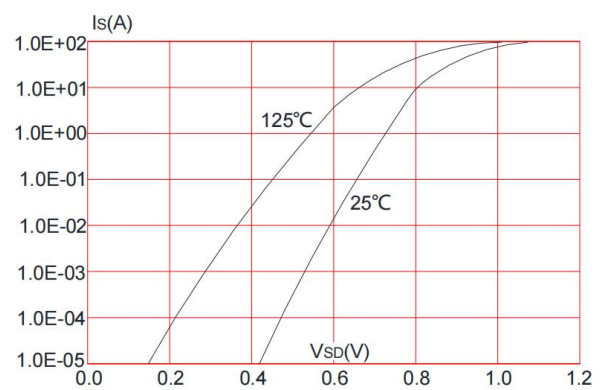


Figure 5: Gate Charge Characteristics

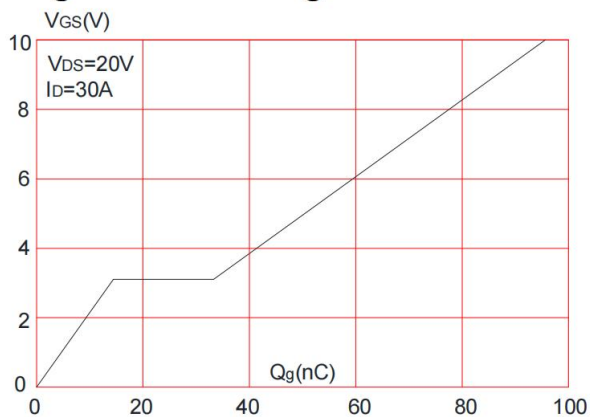
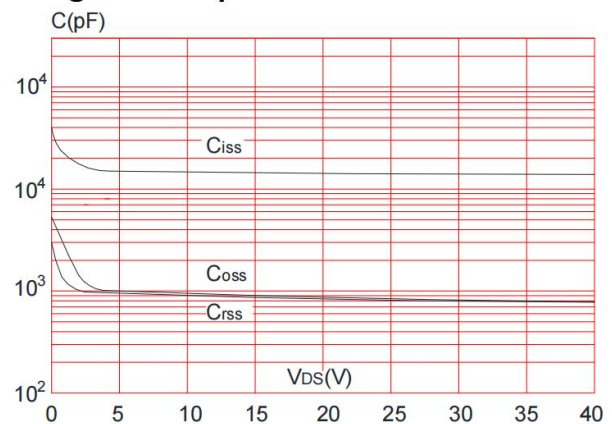
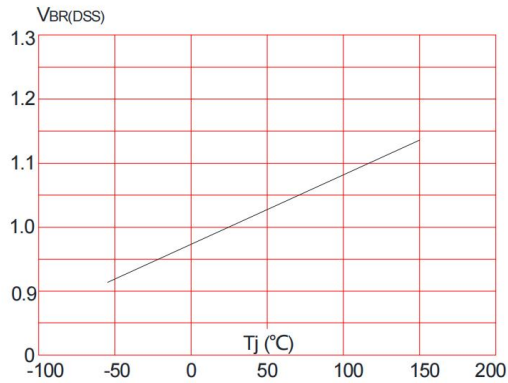


Figure 6: Capacitance Characteristics

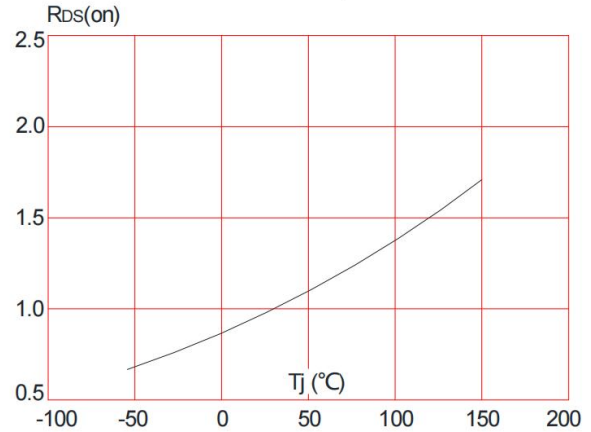


## TYPICAL PERFORMANCE CHARACTERISTICS

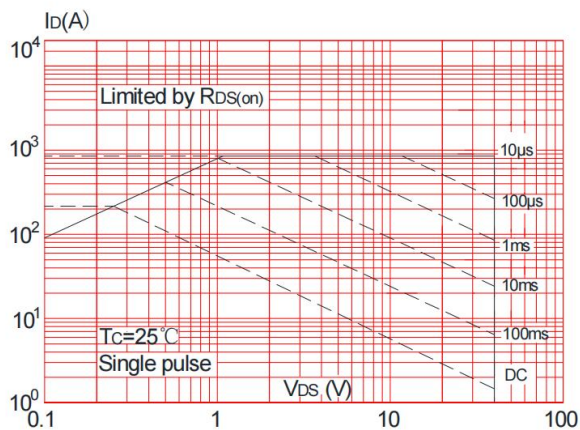
**Figure 7: Normalized Breakdown voltage vs. Junction Temperature**



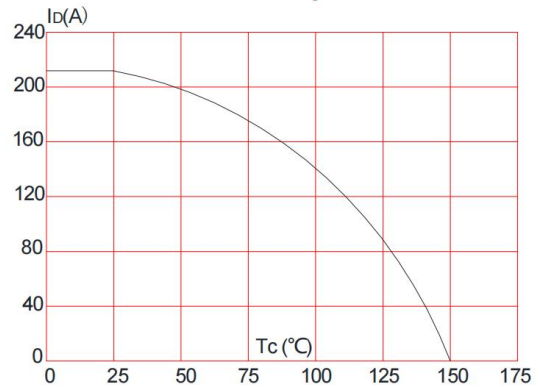
**Figure 8: Normalized on Resistance vs. Junction Temperature**



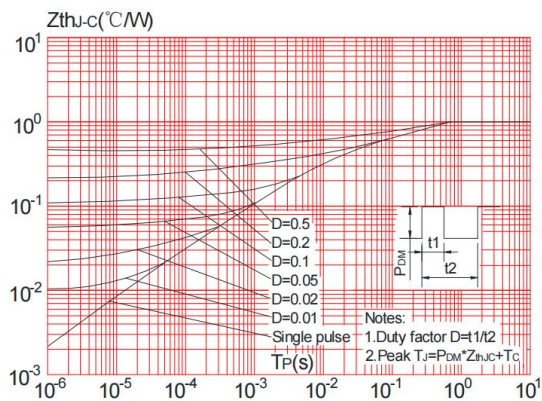
**Figure 9: Maximum Safe Operating Area**



**Figure 10: Maximum Continuous Drain Current vs. Case Temperature**



**Figure 11: Normalized Maximum Transient Thermal Impedance**



## TEST CIRCUIT

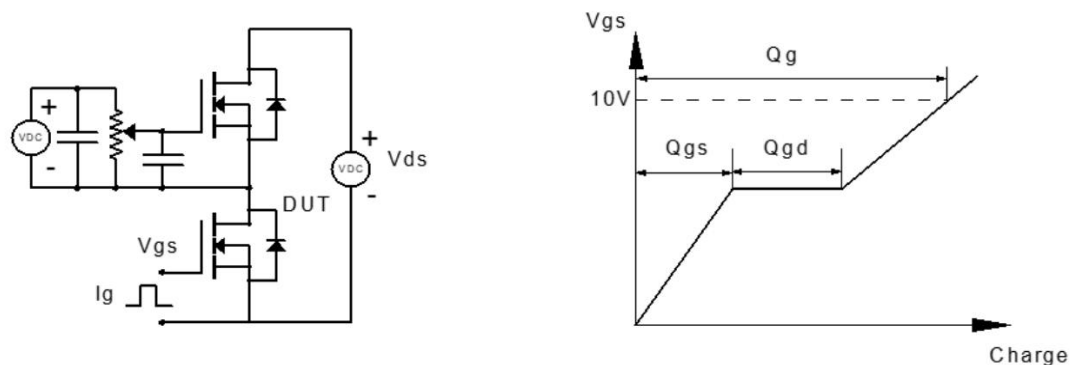


Figure 12: Gate Charge Test Circuit & Waveform

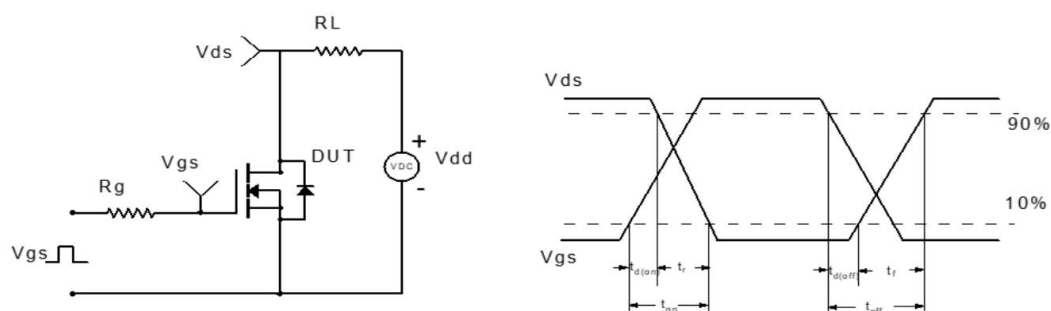


Figure 13: Resistive Switching Test Circuit & Waveform

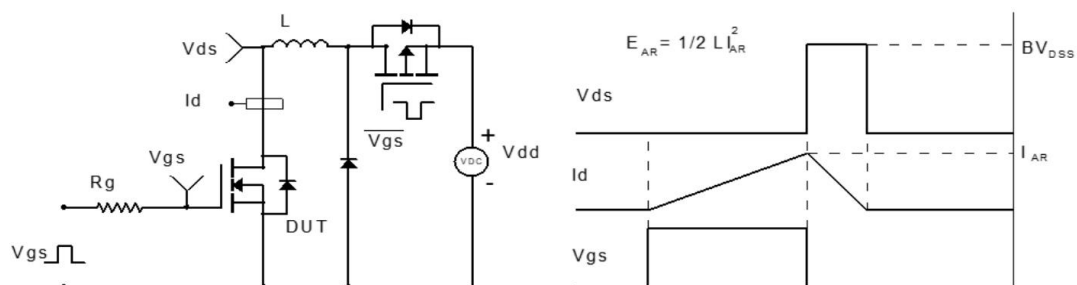
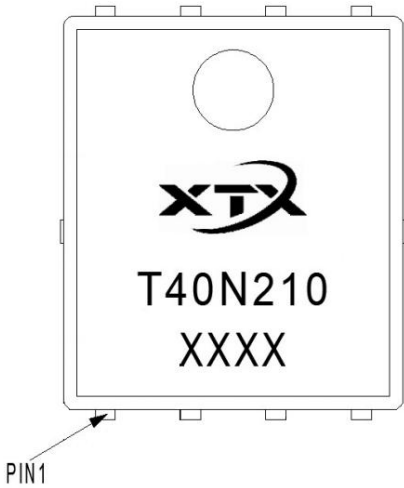


Figure 14: Unclamped Inductive Switching Test Circuit & Waveform

MARKING INFORMATION



1st Line: XTX Logo

2nd Line: Part Number (T40N210)

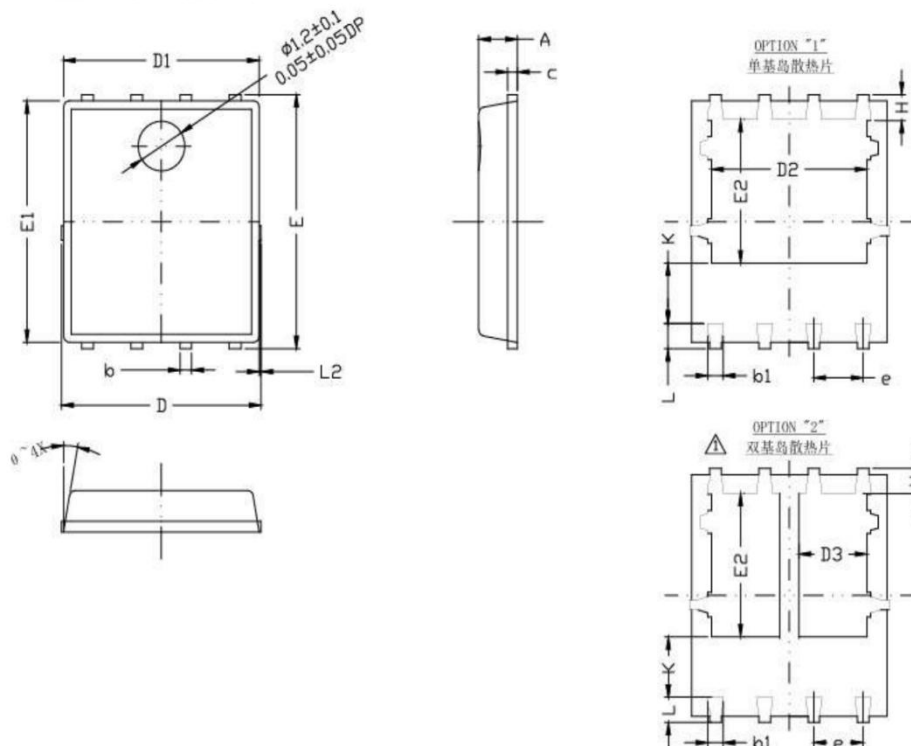
3rd Line: Date Code (XXXX)

XX: Year

XX: Week (01 to 53)

Year	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	21	22	23	24	25	26	27	28	29	30	31	32	33

# DETAIL PACKAGE OUTLINE DRAWING (PDFN5\*6-8L)



SYMBOL	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.25	0.30	0.35
b1	0.30	0.40	0.45
c	0.22	0.25	0.28
D	-	-	5.30
D1	4.90	5.05	5.20
D2	4.01 REF.		
D3	1.75 REF.		
E	6.00	6.15	6.30
E1	5.70	5.85	6.00
E2	3.48 REF.		
e	1.10	1.27	1.40
H	0.61	0.71	0.81
K	1.10	-	-
L	0.51	0.61	0.71
L2	-	-	0.10
$\theta$	8°	-	12°



**REVISION HISTORY**

Number	Description
Rev 1.0	BRT40N210P2 datasheet release